

ABSTRACT OF THE DISCLOSURE

An actual pattern size is obtained from a processing carried out at a pivotal point which is an exposing condition resulting in little variation in pattern size even with variations in focus of exposing light. An operation is inputted on a switching screen displayed for selecting whether to set a substrate treating condition according to a pivotal shift which is a difference between the actual pattern size and a mask pattern size. When setting a substrate treating condition according to the pivotal shift, an operation is inputted on a type selecting screen displayed for selecting a type from different types of substrate treating conditions including the types of photoresist, the types of pattern size and the types of pattern form. Then, an operation is inputted on a substrate treating condition selecting screen displayed for selecting one substrate treating condition from a plurality of substrate treating conditions of the same type selected on the type selecting screen. An optimal developing time is derived from a correlation between a developing time with the selected substrate treating condition and the pivotal shift, whereby a pattern size may be set simply.